

*Sub D1  
Cancel*

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

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*Sub D2  
C2*

6. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition; and

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

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*Sub D3  
C3*

11. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition using TEOS; and

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

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*Sub D4  
C4*

30. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a crystalline semiconductor film over a substrate;  
forming an insulating film comprising silicon oxide on said crystalline semiconductor film by a vapor phase deposition; and